

REPLACEMENT CLAIMS

G1 Sub H1
1. (Amended) A semiconductor isolation structure comprising:

a substrate, the substrate comprising a surface;
a first device and a second device formed within the substrate;
an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:
a deep region which extends into the substrate, the deep region comprising a deep region cross-sectional area;
a shallow region which extends to the surface of the substrate, the shallow region comprising:
a protective outer wall adjacent to the substrate;
an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall; and
the shallow region having a shallow region cross-sectional area;
wherein the deep region cross-sectional area is greater than the shallow region cross-sectional area, the deep region abutting only a single shallow region.

G2 Sub H2
5. (Amended) A semiconductor isolation structure comprising:

a substrate, the substrate comprising a surface;
a first device and a second device formed within the substrate;
an isolation region formed within the substrate between the first device and the second device, the isolation region comprising:
a deep region which extends into the substrate, the deep region comprising an oxide;
a shallow region which extends to the surface of the substrate, the shallow region comprising:
a protective outer wall adjacent to the substrate,
an inner sealing wall located exclusively within the shallow region and adjacent to the protective outer wall;
wherein the deep region abuts only a single shallow region.